

# Ji-Hui Yang

## List of Publications by Year in descending order

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Version: 2024-02-01

39  
papers

4,770  
citations

279798

23  
h-index

315739

38  
g-index

39  
all docs

39  
docs citations

39  
times ranked

6877  
citing authors

#	ARTICLE	IF	CITATIONS
1	Semiconductor-to-metal transition from monolayer to bilayer blue phosphorous induced by extremely strong interlayer coupling: a first-principles study. <i>Nanoscale</i> , 2022, 14, 4082-4088.	5.6	3
2	Enhancing Hole Density and Suppressing Recombination Centers through Illumination in Kesterite Thin Film Solar Cells. <i>Journal of Physical Chemistry Letters</i> , 2022, 13, 2474-2478.	4.6	3
3	Computational Study of the $C_{2}P_{4}$ Monolayer as a Stable Two-Dimensional Material with High Carrier Mobility: Implications for Nanoelectronic Devices. <i>ACS Applied Nano Materials</i> , 2022, 5, 6972-6979.	5.0	4
4	Semiconducting $\hat{1}\hat{2}$ -boron sheet with high mobility and low all-boron contact resistance: a first-principles study. <i>Nanoscale</i> , 2021, 13, 8474-8480.	5.6	15
5	Dimensionality-Inhibited Chemical Doping in Two-Dimensional Semiconductors: The Phosphorene and $MoS_{2}$ from Charge-Correction Method. <i>Nano Letters</i> , 2021, 21, 6711-6717.	9.1	14
6	Unusual defect properties in multivalent perovskite $Cs_{2}Mg_{6}I_{8}A$ : A first-principles study. <i>Physical Review Materials</i> , 2021, 5, .	2.4	8
7	Unusual interlayer coupling in layered Cu-based ternary chalcogenides $CuMCh_{2}$ (M = Sb, ) <i>TJ ETQq1 1 0.784314 rgBT /Over</i>	5.6	17
8	Fully Boron-Sheet-Based Field Effect Transistors from First-Principles: Inverse Design of Semiconducting Boron Sheets. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 576-584.	4.6	14
9	Self-consistently determining structures of charged defects and defect ionization energies in low-dimensional semiconductors. <i>Physical Review B</i> , 2020, 102, .	3.2	9
10	Stacking induced indirect-to-direct bandgap transition in layered group-IV monochalcogenides for ideal optoelectronics. <i>Journal of Materials Chemistry C</i> , 2019, 7, 11858-11867.	5.5	10
11	Cu-Zn disorder in stoichiometric and non-stoichiometric $Cu_{2}ZnSnS_{4}/Cu_{2}ZnSnSe_{4}$ . <i>AIP Advances</i> , 2019, 9, .	1.3	11
12	Two-Level Quantum Systems in Two-Dimensional Materials for Single Photon Emission. <i>Nano Letters</i> , 2019, 19, 408-414.	9.1	59
13	Unusual Negative Formation Enthalpies and Atomic Ordering in Isovalent Alloys of Transition Metal Dichalcogenide Monolayers. <i>Chemistry of Materials</i> , 2018, 30, 1547-1555.	6.7	20
14	Design of Lead-Free Inorganic Halide Perovskites for Solar Cells via Cation-Transmutation. <i>Journal of the American Chemical Society</i> , 2017, 139, 2630-2638.	13.7	714
15	Antimony Diffusion in CdTe. <i>IEEE Journal of Photovoltaics</i> , 2017, 7, 870-873.	2.5	11
16	Earth-Abundant and Non-Toxic $SiX$ (X = S, Se) Monolayers as Highly Efficient Thermoelectric Materials. <i>Journal of Physical Chemistry C</i> , 2017, 121, 123-128.	3.1	41
17	Design of Two-Dimensional Graphene-like Dirac Materials $\hat{1}^{2}XB_{5}$ (X = H, F,) <i>TJ ETQq1 1 0.784314 rgBT /Over</i> 4594-4599.	4.6	23
18	Carrier providers or killers: The case of Cu defects in CdTe. <i>Applied Physics Letters</i> , 2017, 111, 042106.	3.3	22

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19	Notice of Removal Antimony diffusion in CdTe. , 2017, , .		0
20	Fast self-diffusion of ions in CH <sub>3</sub> NH <sub>3</sub> Pb <sub>3</sub> : the interstitially mechanism versus vacancy-assisted mechanism. Journal of Materials Chemistry A, 2016, 4, 13105-13112.	10.3	74
21	Phosphorus Diffusion Mechanisms and Deep Incorporation in Polycrystalline and Single-Crystalline CdTe. Physical Review Applied, 2016, 5, .	3.8	26
22	Review on first-principles study of defect properties of CdTe as a solar cell absorber. Semiconductor Science and Technology, 2016, 31, 083002.	2.0	109
23	Chemical Trends of Electronic Properties of Two-Dimensional Halide Perovskites and Their Potential Applications for Electronics and Optoelectronics. Journal of Physical Chemistry C, 2016, 120, 24682-24687.	3.1	41
24	Non-Radiative Carrier Recombination Enhanced by Two-Level Process: A First-Principles Study. Scientific Reports, 2016, 6, 21712.	3.3	74
25	Two-Dimensional SiS Layers with Promising Electronic and Optoelectronic Properties: Theoretical Prediction. Nano Letters, 2016, 16, 1110-1117.	9.1	149
26	Self-regulation of charged defect compensation and formation energy pinning in semiconductors. Scientific Reports, 2015, 5, 16977.	3.3	56
27	First-principles multiple-barrier diffusion theory: The case study of interstitial diffusion in CdTe. Physical Review B, 2015, 91, .	3.2	33
28	Enhanced p-type dopability of P and As in CdTe using non-equilibrium thermal processing. Journal of Applied Physics, 2015, 118, .	2.5	60
29	Halide perovskite materials for solar cells: a theoretical review. Journal of Materials Chemistry A, 2015, 3, 8926-8942.	10.3	1,114
30	Defect properties of Sb- and Bi-doped CuInSe <sub>2</sub> : The effect of the deep lone-pair <i>s</i> states. Applied Physics Letters, 2014, 105, .	3.3	21
31	Tuning the Fermi level beyond the equilibrium doping limit through quenching: The case of CdTe. Physical Review B, 2014, 90, .	3.2	66
32	What are grain boundary structures in graphene?. Nanoscale, 2014, 6, 4309-4315.	5.6	34
33	Predicting Two-Dimensional Boron-Carbon Compounds by the Global Optimization Method. Journal of the American Chemical Society, 2011, 133, 16285-16290.	13.7	242
34	Compositional dependence of structural and electronic properties of Cu <sub>2</sub> ZnSn(S,Se) <sub>4</sub> . Scientific Reports, 2015, 5, 16977.	3.3	399
35	Compositional dependence of structural and electronic properties of Sn <sub>2</sub> ZnSn(S,Se) <sub>4</sub> . Scientific Reports, 2015, 5, 16977.	3.3	399

#	ARTICLE	IF	CITATIONS
37	Effective band gap narrowing of anatase TiO <sub>2</sub> by strain along a soft crystal direction. Applied Physics Letters, 2010, 96, .	3.3	185
38	Intrinsic point defects and complexes in the quaternary kesterite semiconductor $Cu_2ZnSnS_4$ Physical Review B, 2010, 81, .	3.2	624
39	Electronic structure and phase stability of MgTe, ZnTe, CdTe, and their alloys in the <i>B</i> <sub>3</sub> , <i>B</i> <sub>4</sub> , and <i>B</i> <sub>8</sub> structures. Physical Review B, 2009, 79, .	3.2	55